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ABSTRACT OF THE DISCLOSURE

A dry etching method for etching a surface of a substrate with plasma of mixed gas including i) gas that is reactive to the material of the substrate, and ii) inert gas. Accumulation of reaction products between the substrate and the reactive gas ions on the substrate is effectively eliminated by the ions of the inert gas plasma. Accordingly the etching rate of the substrate is not lowered. Silicon carbide (SiC) is one of the most suitable object of the plasma etching of the present invention, since it is hard to engrave by conventional dry etching methods.

